

1 The method of preparing a carbon-doped group III-V compound  
2 semiconductor crystal according to claim 1, wherein said boron  
3 oxide substance contains boron oxide and 10 to 500 wt. ppm of  
4 water, and said method further comprises:

5 softening said boron oxide substance and contacting said  
6 softened boron oxide substance with said solid carbon whereby at  
7 least some of said carbon reacts with said water and dissolves  
8 in said boron oxide substance, before said step of melting said  
9 compound raw material;

10 then, after said step of melting said compound raw material,  
11 contacting said melted compound raw material with said softened  
12 boron oxide substance having said carbon dissolved therein,  
13 whereby at least some of said carbon dissolves from said softened  
14 boron oxide substance into said melted compound raw material.

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1 The method of preparing a carbon-doped group III-V compound  
2 semiconductor crystal according to claim 24, wherein said boron  
3 oxide substance contains not more than 300 ppm of said water.

REMARKS:

- 1) The issuance of a clarified replacement Office Action and re-starting of the period for response on December 8, 1998 is appreciated.